

ABSTRACT OF THE DISCLOSURE

An alignment component is formed on a substrate of a semiconductor material which is N- or P-doped. A metal layer is deposited over the substrate and the alignment component. The metal layer is reacted with the semiconductor material of the substrate to form two silicide regions, on opposing sides of the alignment component, which extend up to the alignment component. The alignment component is then replaced with a gate which extends up to the silicide regions. A transistor results wherein inner surfaces of the silicide regions, facing one another, are in direct contact with the N- or P-doped semiconductor material of the substrate and therefore have a low series resistance between them.